# An Ultrasonic Energy Harvesting IC Providing Adjustable Bias Voltage for Pre-Charged CMUT

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Abstract—Ultrasonic wireless power transmission (WPT) using pre-charged capacitive micromachined transducers (CMUT) is drawing great attention due to the easy integration of CMUT with CMOS techniques. Here, we present an integrated circuit (IC) that interfaces with a pre-charged CMUT device for ultrasonic energy harvesting. We implemented an adaptive high voltage charge pump (HVCP) in the proposed IC, which features low power, overvoltage stress (OVS) robustness, and a wide output range. The ultrasonic energy harvesting IC is fabricated in the 180 nm HV BCD process and occupies a 2 × 2.5 mm<sup>2</sup> silicon area. The adaptive HVCP offers a  $2 \times -12 \times$  voltage conversion ratio (VCR), thereby providing a wide bias voltage range of 4V – 44V for the pre-charged CMUT. Moreover, a VCR tunning finite state machine (FSM) implemented in the proposed IC can dynamically adjust the VCR to stabilize the HVCP output (i.e., the pre-charged CMUT bias voltage) to a target voltage in a closed-loop manner. Such a closed-loop control mechanism improves the tolerance of the proposed IC to the received power variation caused by misalignments, amount of transmitted power change, and/or load variation. Besides, the proposed ultrasonic energy harvesting IC has an average power consumption of 35 µW  $-554 \mu W$  corresponding to the HVCP output from 4 V - 44 V. The CMUT device with a local surface acoustic intensity of 3.78 mW/mm<sup>2</sup>, which is well below the FDA limit for power flux (7.2) mW/mm<sup>2</sup>), can deliver sufficient power to the IC.

Keywords—ultrasonic energy harvesting, wireless power transmission, high voltage charge pump, pre-charged CMUT

## I. INTRODUCTION

MPLANTABLE medical devices (IMD) that interface with the nervous system for recording and stimulating neural activities help deepen our understanding of the brain, revolutionize the way that the human interacts with computers and robotics, and enable neuromodulation-based therapies for neurological diseases and conditions, e.g., Alzheimer's disease, Parkinson's disease, and Epilepsy, which currently cannot be treated adequately with medication alone [1-3]. Wireless power

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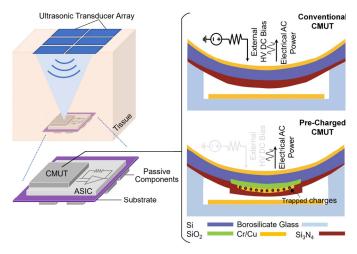


Fig. 1. Conceptual view of the ultrasonically powered IMD that incorporates a pre-charged CMUT to receive ultrasonic power at deep tissue.

transmission (WPT) is a key feature that can eliminate the tethering effects and the requirement of bulky batteries, bringing the IMDs closer to clinical use [1-3]. So far electromagnetic (EM) and ultrasonic WPT approaches have been commonly used, each of which has its advantages for a particular application [4, 5].

Near-field inductive link and far-field RF link are two popular implementations of the EM WPT approach. Several inductive link designs implemented in wireless power cages enable high efficient WPT to an IMD carried by a small animal subject (e.g., a rodent) while the subject is freely moving inside the cage [6-8]. It is well understood that device miniaturization is significant in reducing device invasiveness to the tissue [1-3]. However, WPT to mm/sub-mm sized IMDs is challenging. The weak coupling between transmitter (Tx) and receiver (Rx) coils and stringent size constraints affects power transfer efficiency (PTE) and the amount of power delivered to the load (PDL) [9, 10]. To overcome these challenges, various inductive link configurations and optimization methods have been proposed [11-17]. Unlike large coils, tiny coils tend to have their optimal O-factor at hundreds of MHz or even in GHz bands. However, the specific absorption rate (SAR) of the EM field in the body increases along with the carrier frequency [18]. This will limit the WPT depth in tissue and impose stringent safety constraints. Far-field RF links usually offer long-distance WPT through the air and have been used significantly in WPT to IMDs [19, 20]. However, most of the proposed designs are in the GHz band, which imposes more challenges on SAR limits.

Compared to EM WPT, the ultrasonic WPT approach has distinct advantages of shorter wavelength, lower attenuation in body tissue, and little EM interference [4, 5]. Thus, ultrasonic WPT has been widely used to power miniature IMDs in deep tissue without surpassing the FDA ultrasound intensity limit [21-23]. It is also feasible to apply beamforming of ultrasonic energy to mm-sized focal spots at large depths in the body [21, 22]. A great number of existing ultrasonic WPT designs use piezoelectric transducers [24-28]. In [24], the ultrasonically powered implant that incorporates a piezo and an integrated circuit (IC) can receive input power of several milliwatts with dimensions of  $2\times3\times6.5$  mm<sup>3</sup> at the tissue depth of 10.5 cm from a commercial Tx transducer operating at 1.3 MHz – 1.5 MHz. In the ultrasonically powered neural stimulation system presented in [25], a 1.7 mm<sup>3</sup> stimulator receives power at 18 mm in vivo depth through an ultrasonic link at 1.85 MHz. The ultrasonic link in [26] operates at 2 MHz, delivering ~140 μW amount of power to a 4.5mm<sup>3</sup> ultrasonic luminescence oxygen sensor implanted at 5 cm tissue depth. There are also ultrasonic WPT systems with phased array beamforming techniques that enable wireless powering of multiple implants [27, 28].

The advent of microelectromechanical system (MEMS) technology has brought about the development of capacitive micromachined ultrasonic transducer (CMUT). CMUT can be an alternative technology to the piezoelectric transduces with its distinct advantage of easy integration with electronic circuits [29-31]. Such feasibility is significant in IMD miniaturization. CMUT also features ease of fabrication and the possibility of achieving broader bandwidth [29-31]. In Fig. 1, the conceptual view of CMUT-based ultrasonic WPT shows that the CMUTon-CMOS integration reduces the number of electrical connections leading to a smaller device form factor [32, 33]. This approach also minimizes parasitic capacitances, which would enhance the PTE of the ultrasonic link [32, 33]. However, standard CMUT requires an extra bias voltage in the order of several tens of volts to hundred volts, which sets a barrier for IMD power reduction [29-31]. To eliminate or moderate the requirement of the high DC bias, pre-charged CMUT is developed and used as the power Rx component for ultrasonic energy harvesting [34-36].

Fig. 1 shows a CMUT with a metal floating gate [36]. A chromium/gold layer is introduced inside the CMUT structure as a floating electrode to trap charges. The trapped charges replace the DC bias to produce a static plate deflection in the CMUT device, thus enabling CMUT to receive the amount of power that is just enough for ultrasonic energy harvesting circuits to start up without an external bias voltage. Once the circuits start up successfully, they, in turn, can provide a bias voltage, a few volts to tens of volts, such that the pre-charge CMUT can operate at its optimal condition in terms of maximum output power. The bias voltage that the circuits can provide varies as the amount of received power changes. To stabilize the bias voltage in different wireless power conditions, it would be significant that the ultrasonic energy harvesting circuits can provide a bias voltage dynamically adjustable in a closed-loop manner for the pre-charged CMUT.

Hence, we propose a novel ultrasonic energy harvesting IC, in which a low power, overstress robust, adaptive high voltage charge pump (HVCP) provides an adjustable bias voltage of 4 V – 44 V for the pre-charged CMUT. Such a wide bias voltage range enables the IC to meet the needs of the bias for a variety of pre-charge conditions. The HVCP is also applicable for electrical stimulation as it can offer sufficient compliance voltage for the stimulator. To the best of our knowledge, this is the first IC that interfaces with pre-charged CMUT for ultrasonic energy harvesting. An overview of the proposed ultrasonic energy harvesting IC is given in Section II. Section III presents the acoustic measurement setup. Section IV shows the IC characterization, followed by a discussion and a conclusion.

## II. ULTRASONIC ENERGY HARVESTING IC OVERVIEW

The block diagram of the proposed ultrasonic energy harvesting IC is shown in Fig. 2. A voltage doubler converts the AC input voltage,  $V_{\rm AC}$ , to a DC voltage,  $V_{\rm DBR}$ , which is further regulated by a low-dropout regulator (LDO), resulting in a supply voltage of  $V_{\rm DD} = 1.8 \, \rm V$ . A bandgap reference (BGR) and bias generator provide bias voltages/currents for the remaining circuits. As  $V_{\rm DD}$  increases to a certain value, a power-on-reset (POR) flag raises to trigger digital control circuits. The HVCP employs a switched-capacitor-based structure in each stage, in

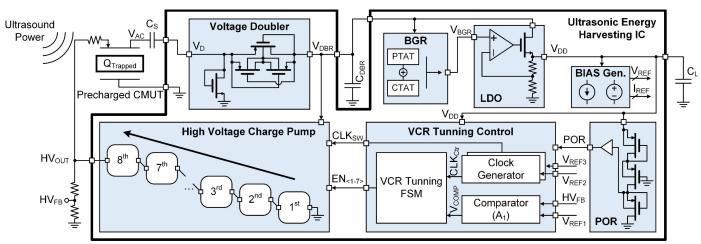


Fig. 2. Block diagram of the ultrasonic energy harvesting IC.

which a clock,  $CLK_{\rm SW}$ , controls the capacitor switching, upconverting the HVCP input (i.e.,  $V_{\rm DBR}$ ) to  $HV_{\rm OUT}$  (i.e., the bias voltage for the CMUT). The voltage conversion ratio (VCR) tunning control circuits adjust the VCR of the HVCP to stabilize  $HV_{\rm OUT}$  to a target voltage in a closed-loop manner. More specifically, the VCR tunning finite-state-machine (FSM), controlled by the clock,  $CLK_{\rm Ctr}$ , generates controls bits,  $EN_{<1-7>}$ , based on the comparison result of the divided  $HV_{\rm OUT}$ ,  $HV_{\rm FB}$ , and a reference voltage,  $V_{\rm REF1}$ , to enable/disable the 8 stages in the HVCP.

Fig. 3a shows the HVCP schematic, which consists of 8 cascaded stages, i.e., the first four +1 cells and the last four +2 cells. As shown in Fig. 3b, the design of the +1 cell refers to the cross-coupled charge pump structure, in which the clocks,  $\phi_1$  and  $\phi_2$ , generated from non-overlapping clocks,  $CLK_P$  and  $CLK_N$ , oscillate between  $V_{DBR}$  and GND. The +2 cell is configured as two +1 cells connected in series. Using non-overlapping clocks can reduce switching loss and flow-back leakage current, thereby saving the power consumption of HVCP. In Fig. 3c, the non-overlapping clocks,  $CLK_P$  and  $CLK_N$ , are generated from  $CLK_{SW}$  and stepped up from  $V_{DD}$  to  $V_{DBR}$ . The delay elements, i.e., inverters, influence the delays between  $CLK_P$  and  $CLK_N$ . We designed the size and the number of the

inverters to ensure sufficient non-overlapping between  $CLK_P$  and  $CLK_N$ .

The proposed HVCP features overvoltage stress (OVS) robustness. In the cross-coupled charge pump structure, the maximum gate-to-source voltage is  $V_{\rm DBR}$ , which is below the breakdown voltage. Such an HVCP cell design can mitigate the gate-to-source OVS issue. To tolerate the high drain-to-source voltage, 70V MOSFETs are used in HVCP cells and their corresponding switches,  $S_1$ - $S_7$ . Each cell, except the  $8^{\rm th}$  cell, has its HV switch connecting between the cell output and GND. If the switch is connected between the output of the  $n^{\rm th}$  cell and the input of the  $(n+1)^{\rm th}$  cell, boost-strap drivers are required to drive the gate of the floating switch MOSFET [37]. The current switch configuration simplifies the switch driver, thus reducing the HVCP power consumption.

 $EN_{<1-7>}$  selectively control  $S_1$ - $S_7$  to set VCR as  $2\times$ ,  $4\times$ ,  $6\times$ ,  $8\times$ ,  $9\times$ ,  $10\times$ ,  $11\times$ , or  $12\times$ . Since the supply voltage of the charge pump cells and clocks in the HVCP is  $V_{\rm DBR}$ , we can calculate  $HV_{\rm OUT}$  using  $HV_{\rm OUT} = V_{\rm DBR} \times {\rm VCR} - {\rm voltage}$  loss. In Fig. 3d, we present three examples of VCR settings via  $EN_{<1-7>}$  controls. We enable a cell by turning off its HV switch at the output, otherwise, we need to turn on the switch to disable the cell. As we can see, the  $8^{\rm th}$  cell is always enabled. To set the VCR to a certain value, we need to enable the last few cells by turning

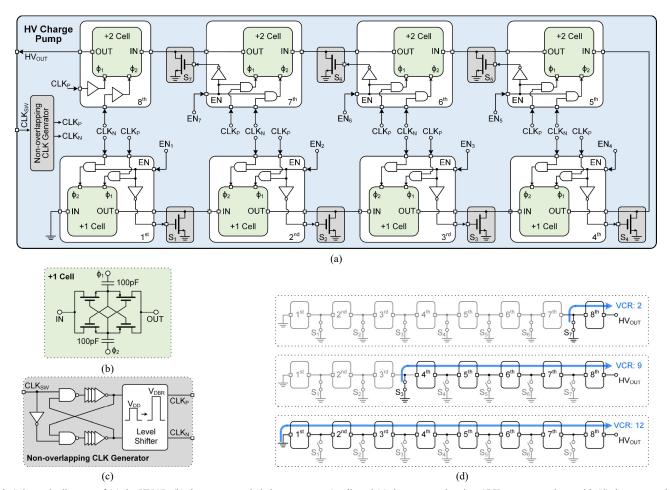


Fig. 3. Schematic diagram of (a) the HVCP, (b) the cross-coupled charge pump +1 cell, and (c) the non-overlapping CLK generator, along with (d) three examples of VCR tunning via control signals  $EN_{<1.7>}$ .

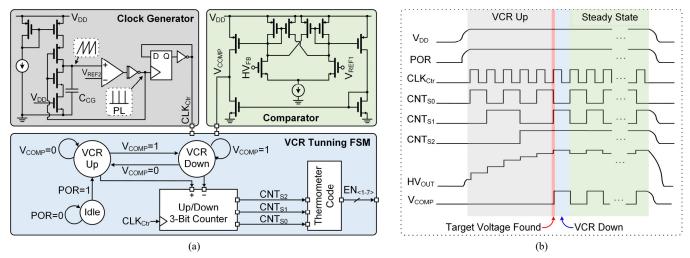


Fig. 4. (a) Schematic diagrams of the clock generator, the comparator, and the VCR tunning FSM in the VCR tuning control. (b) Timing diagram of the VCR tuning control operation.

their corresponding HV switches off while keeping the remaining switches on. The VCR is set to the maximum when all the cells are enabled by turning  $S_1$ - $S_7$  off. Given that the  $5^{th}$  –  $8^{th}$  cells are +2 cells, if the  $4^{th}$  –  $8^{th}$  cells are enabled by turning  $S_4$  –  $S_7$  off while turning  $S_1$  –  $S_3$  on, VCR is set to 9. If all the switches are on, only the  $8^{th}$  cell is enabled, resulting in VCR being equal to 2.

Fig. 4 shows the schematic and timing diagrams of the VCR tunning control. As shown in Fig. 4a, the VCR tunning control circuits include two clock generators, a comparator, and a VCR tunning finite-state-machine (FSM). The clock generators use the same circuit topology, i.e., comparator-based relaxation oscillator [38]. They provide a 110 kHz clock, CLK<sub>SW</sub>, for the HVCP capacitor switching and a 15 kHz clock,  $CLK_{Ctr}$ , for the control of VCR tunning FSM, respectively. In the clock generator, the comparator output, PL, controls the charging and discharging of the capacitor,  $C_{CG}$ . When PL is low, a constant current from the current source continuously charges  $C_{CG}$  while the voltage across  $C_{CG}$  increases accordingly. When the voltage across  $C_{CG}$  reaches  $V_{REF2}$ , PL goes high. This allows a large current to discharge  $C_{CG}$ , resulting in narrow PL pulses. Then, the frequency divider converts PL pulses to a square wave output. This clock generator is a simple and low-power design.

The VCR tunning FSM has three statuses: *Idle*, *VCR Up*, and *VCR Down*. The comparator compares  $HV_{\rm FB}$  and  $V_{\rm REFI}$ . According to the comparison result,  $V_{\rm COMP}$ , the VCR tuning FSM switches between the three statues at the frequency of  $CLK_{\rm Ctr}$ . The 3-bit counter counts down in the *VCR Down* status while counting up in the *VCR Up* status. The thermometer code circuit converts the counter outputs,  $CNT_{\rm S0}$ - $CNT_{\rm S2}$ , to the 7-bit control signals,  $EN_{<1-7>}$ . The VCR tunning FSM sends  $EN_{<1-7>}$  to the HVCP to selectively enable or disable the HVCP cells, thus adjusting the VCR and stabilizing  $HV_{\rm OUT}$  to a target voltage in a closed-loop.

In Fig. 4b, the timing diagram shows that as the POR flag raises, the VCR tunning starts operation (i.e., the VCR tunning FSM exits the *Idle* status).  $HV_{\rm FB}$  is detected and compared with  $V_{\rm REF1}$  continuously. In the beginning, since  $HV_{\rm OUT}$  is much smaller than its target voltage,  $HV_{\rm FB}$  is lower than  $V_{\rm REF1}$ ,

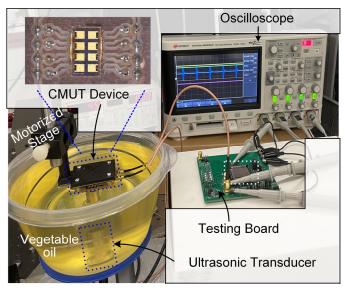


Fig. 5. Acoustic experimental setup: CMUT harvesting ultrasound power to operate the IC while the VCR tunning control stabilizes the CMUT bias voltage at a target voltage.

resulting in  $V_{\text{COMP}} = 0$ . Then, the VCR tunning FSM enters the VCR Up. In the VCR Up status,  $CNT_{S0}$ - $CNT_{S2}$ , in which  $CNT_{S2}$ is the most significant bit (MSB), is counting up, while the number of HVCP cells being enabled is increasing, thus  $HV_{OUT}$ increases step by step towards the target voltage. When  $HV_{OUT}$ reaches the target voltage,  $HV_{\rm FB}$  becomes larger than  $V_{\rm REF1}$ while the comparator flips its output. Since  $V_{\text{COMP}} = 1$  now, the VCR tunning FSM switches to the VCR Down status, in which the counter switches to stepping down mode. Hence, as the number of HVCP cells being enabled reduces, VCR and HVOUT decrease. When  $HV_{OUT}$  becomes smaller than the target voltage, the VCR tuning FSM switches back to the VCR Up status. In steady status, the FSM switches between VCR Up and VCR *Down.* In the meanwhile, as  $CNT_{S0}$ - $CNT_{S2}$  switches between two adjacent values (e.g., "110" and "101" in Fig. 4b), VCR switches between two adjacent ratios, and  $HV_{OUT}$  is bouncing around the target voltage.

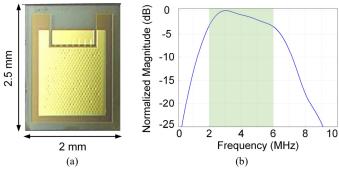


Fig. 6. The implementation of the pre-charged CMUT device (b) measured CMUT frequency response.

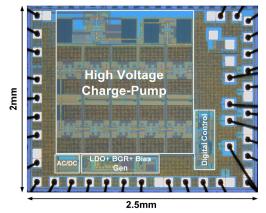


Fig. 7. The micrograph of the fabricated ultrasonic energy harvesting IC.

## III. ACOUSTIC MEASUREMENT

Fig. 5 shows the acoustic measurement setup for extensive characterizations of the proposed IC with ultrasonic powering at a focal depth of 19 mm. Multiple pre-charged CMUT devices are bonded on a printed circuit board (PCB), but only one of them connects to the IC and receives ultrasonic power. The PCB is held by a motorized stage and immersed in vegetable oil. Eventually, the CMUT will be implanted in the subject's body while performing ultrasonic energy harvesting. Vegetable oil is an insulator and also can model the acoustic impedance and loss of soft tissue.

In Fig. 6a, the fabricated single element CMUT includes 318 cells with a diameter of 60  $\mu$ m, resulting in an area of 2 × 2.5 mm², which is designed to be assembled on the chip to be built as a miniature implantable device. In Fig. 6b, the measured frequency response shows that the pre-charged CMUT has a bandwidth of 2 MHz – 6 MHz with a peak at ~ 3 MHz. The details on the design and fabrication of the pre-charged CMUT with a metal floating gate can be found in [36].

A focused single-element commercial ultrasound Tx transducer (OLYMPUS, V325) with a focal distance of 19 mm is mounted at the bottom of the oil tank and delivers ultrasonic power pulses to the CMUT device. Alignment is applied to the motorized stage to locate the CMUT device at the focal point of the Tx transducer. The Tx transducer establishes an ultrasonic link through the oil with the CMUT. We used a hydrophone (ONDA, HGL) for the acoustic intensity measurement. The testing board carries the IC in a CLCC68 package and other

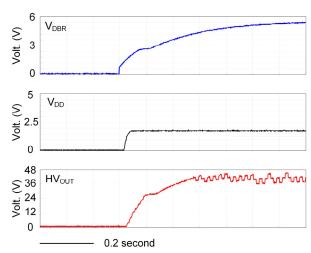


Fig. 8. Transient waveforms of the ultrasonic energy harvesting IC from starting up to going into steady status.



Fig. 9. Power flow from the CMUT to the HVCP in the case the HVCP offering 44V bias voltage for the CMUT.

supporting components (e.g., capacitors). The IC testing board is connected to the CMUT through coaxial cables. The die photo of the ultrasonic energy harvesting IC, shown in Fig. 7, is fabricated in the 180 nm HV BCD process and occupies a  $2 \times 2.5 \text{ mm}^2$  silicon area including testing pads.

The focused ultrasound Tx transducer delivers ultrasonic power pulses with 300 µs pulse duration at a 1 kHz pulse repetition rate to the CMUT. The acoustic intensity at the CMUT is approximately 3.78 mW/mm<sup>2</sup>, which is below the FDA limit of 7.2 mW/mm<sup>2</sup>. In Fig. 8, the measured starting-up transients show the process of  $HV_{OUT}$  reaching the target voltage. We set the target voltage at 44 V by tuning the resistor in the voltage divider of HV<sub>OUT</sub>. Once the CMUT receives ultrasonic power and converts it to usable electrical AC input to power the IC,  $V_{\rm DBR}$  starts increasing. After ~0.05 seconds,  $V_{\rm DBR}$  increases to 2.2 V, and the LDO stabilizes  $V_{\rm DD}$  to 1.8 V. In the meanwhile, the VCR tunning starts operating. The VCR tunning FSM controls VCR step up, increasing HV<sub>OUT</sub>. After 0.28 seconds, as V<sub>DBR</sub> increases to 4 V, HV<sub>OUT</sub> reaches the target voltage of 44 V and goes into steady status, dynamically bouncing within 44 V  $\pm$  3.5 V. During the steady status. It is worthy to mention that even though  $V_{\rm DBR}$  is still increasing,  $HV_{\rm OUT}$  can remain in steady status thanks to the closed-loop control of HV<sub>OUT</sub>.

Fig. 9 shows the power necessary at each stage from the CMUT to the HVCP when the HVCP generates a 44 V bias voltage. Given that the acoustic intensity is 3.78 mW/mm<sup>2</sup> at the CMUT surface and the CMUT active area for receiving energy is ~0.9 mm<sup>2</sup>, the amount of ultrasonic power received by the CMUT is 3.4 mW. Furthermore, the CMUT converts the

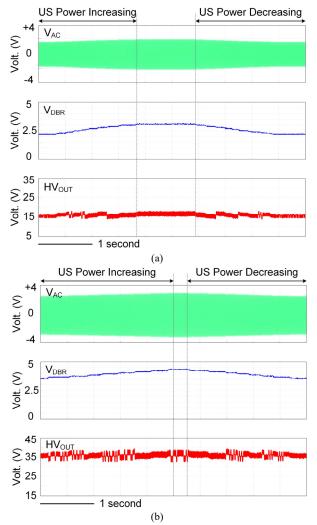


Fig. 10. Transient waveforms of closed-loop control  $HV_{\text{OUT}}$  to the target voltage of (a) 16 V and (b) 36 V when the input ultrasonic power is varying.

ultrasonic power to usable electrical power and delivers 0.554 mW to the IC. With a PTE of 75%, the DC power at the output of the voltage doubler is 0.416 mW, 72% of which is used for HVCP to generate the 44 V bias voltage.

# IV. CIRCUIT CHARACTERIZATION

We set the  $HV_{\rm OUT}$  target voltage to 16 V and 36 V, respectively. Fig. 10 shows the transient waveforms of VCR tunning control when the transmitted ultrasonic power is manually increased and then decreased. In steady status,  $HV_{\rm OUT}$  maintains bouncing within 16 V  $\pm$  1.2 V and 36 V  $\pm$  2.5 V windows, respectively, in the presence of transmitted ultrasonic power varying. In Fig. 10a, the amplitude of the received AC input voltage,  $V_{\rm AC}$ , gradually increases following the transmitted ultrasonic power increase within the first  $\sim$ 2 seconds. Hence, the voltage doubler output,  $V_{\rm DBR}$ , gradually increases. Since  $HV_{\rm OUT}$  =  $V_{\rm DBR}$   $\times$  VCR – voltage loss,  $HV_{\rm OUT}$  shows slight increases, which triggers the closed-loop control. Then, the VCR tunning FSM reduces VCR to compensate for the  $V_{\rm DBR}$  increase. At  $\sim$ 3 seconds, the transmitted ultrasonic power starts decreasing to its original value,  $V_{\rm AC}$  and  $V_{\rm DBR}$  also reduce, while the VCR tunning

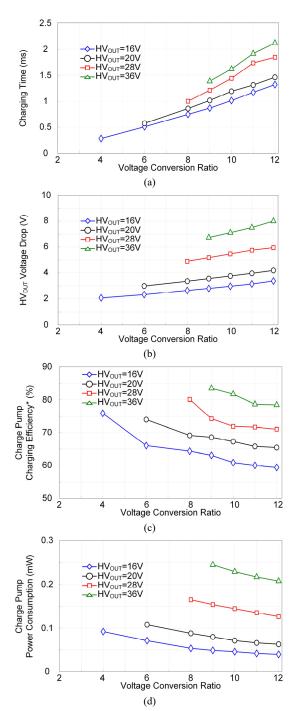


Fig. 11. Measured specifications of HVCP in terms of (a) charging time, (b) voltage drop, (c) charging efficiency, and (d) power consumption.

FSM increases VCR to opposite the  $V_{\rm DBR}$  reduction. During this process, the VCR tunning control stabilizes  $HV_{\rm OUT}$  to the target voltage of 16 V with an offset of  $\pm$  1.2 V. In Fig. 10b, the target voltage is set to 36 V. Higher  $V_{\rm AC}$  and  $V_{\rm DBR}$  are required for  $HV_{\rm OUT}$  to reach the target voltage. In the steady status, since VCR switches between two adjacent ratios,  $HV_{\rm OUT}$  bounds around 36 V with an offset of  $\pm$  2.5 V. The  $HV_{\rm OUT}$  offset is determined by  $V_{\rm DBR}$ . Hence, the higher  $V_{\rm DBR}$  is, the larger the offset is. Several reasons would influence the amount of received power, such as misalignments, the amount of

TABLE I: MEASURED SPECIFICATIONS OF THE ULTRASONIC ENERGY HARVESTING IC

| IC Overview                              |  |  |  |  |  |  |  |
|--|--|--|--|--|--|--|--|
| Chip area                                | $2 \times 2.5 \text{ mm}^2$                        |  |  |  |  |  |  |
| A  | $35 \mu W @ HV_{OUT} = 4 V$                        |  |  |  |  |  |  |
| Average power consumption                | $554 \mu \text{W} @ HV_{\text{OUT}} = 44 \text{V}$ |  |  |  |  |  |  |
| Charge-Pur                               | np Circuit   |  |  |  |  |  |  |
| $HV_{\text{OUT}}$ range                  | 4 V - 44 V   |  |  |  |  |  |  |
| Charging efficiency*                     | 55% - 89%  |  |  |  |  |  |  |
| Charging time*                           | 0.07  ms - 2.6  ms                                 |  |  |  |  |  |  |
| Voltage drop*                            | 0.4  V - 9  V                                      |  |  |  |  |  |  |
| Power consumption*                       | $6 \mu W - 300 \mu W$                              |  |  |  |  |  |  |
| $HV_{ m OUT}$ offset $^*$                | 0.8  V - 3  V                                      |  |  |  |  |  |  |
| AC-DC Volta                              | age Doubler  |  |  |  |  |  |  |
| Efficiency vs. frequency                 | 60% - 79%  |  |  |  |  |  |  |
| Efficiency vs. V <sub>AC</sub> amplitude | 70% - 76%  |  |  |  |  |  |  |
| Efficiency vs. load power                | 73% - 79%  |  |  |  |  |  |  |
| CMUT                                     | Device   |  |  |  |  |  |  |
| CMUT device size                         | $2 \times 2.5 \text{ mm}^2$                        |  |  |  |  |  |  |
| Collapse voltage                         | 60  V - 65  V                                      |  |  |  |  |  |  |
| Bandwidth                                | 2  MHz - 6  MHz                                    |  |  |  |  |  |  |

<sup>\*</sup>The HVCP performance when  $HV_{\rm OUT}$  changes from 4 V to 44 V.

transmitted power variation, and load variation. The importance is to verify the robustness of the ultrasonic powering in the presence of the received power varying. The results in Fig. 10 show the compensation ability of the closed-loop VCR tunning control to the disturbs in the received power amount.

Fig. 11 shows the measured HVCP specifications at different target voltages, which are practical bias voltages for pre-charged CMUT in most cases. The HVCP drives a capacitive load of 100 pF, i.e., the equivalent capacitance of CMUT. Each curve represents an HVCP specification measured at different VCRs for the same  $HV_{\rm OUT}$  target voltage. To meet a certain target voltage,  $HV_{\rm OUT}$  requires a lower  $V_{\rm DBR}$  as the VCR increases. Besides, for the same VCR, a higher  $HV_{\rm OUT}$  target voltage requires a larger  $V_{\rm DBR}$ .

As shown in Fig. 11a,  $HV_{\rm OUT}$  needs a longer time to reach a higher target voltage for the same VCR. This is because the required  $V_{\rm DBR}$  is larger and toggling the capacitors between  $V_{\rm DBR}$  and GND in each HVSP cell takes a longer time. On the other hand, as the VCR increases, the HVCP spends a longer time charging the CMUT to reach the target voltage because the impedance looking into the output of the HVCP increases. Charging time within 0.285 ms – 2.1 ms is measured.

The voltage loss from each stage adds up at the HVCP output. In Fig. 11b, for the same  $HV_{\rm OUT}$  target voltage when the VCR increases, the  $HV_{\rm OUT}$  drop increases. At the same VCR, the  $HV_{\rm OUT}$  drop increases as the  $HV_{\rm OUT}$  target voltage increases. The step size  $HV_{\rm OUT}$  increasing is decided by  $V_{\rm DBR}$ . A larger  $HV_{\rm OUT}$  requires a larger  $V_{\rm DBR}$ . As the step size increases, the  $HV_{\rm OUT}$  drop from each stage increases. We measured that the  $HV_{\rm OUT}$  drop is within the range of 2 V - 8 V.

In Fig. 11c, the measured charging efficiency is 59%–83%. The charging efficiency is calculated as the stored DC energy in the 100 pF equivalent capacitance of CMUT over the total input energy of the HVCP during the charging period. For each curve, larger VCR results in lower charging efficiency for two reasons. First, the  $HV_{\rm OUT}$  drop adds up from each stage and increases. Second, the impedance looking into the HVCP output increases as the VCR increase. On the other hand, the charging efficiency

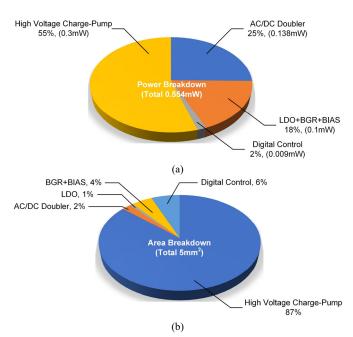


Fig. 12. (a) Average power consumption and (b) silicon area of the main circuits when  $HV_{OUT} = 44 \text{ V}$  with VCR = 12.

increases as  $HV_{\text{OUT}}$  increases at the same VCR because the amount of the output energy increase is larger than that of the energy consumption.

Thanks to the simplified switch driver design, the HVCP including digital control and drivers has a low power consumption of 0.04 mW - 0.24 mW when  $HV_{\rm OUT} = 16$  V - 36 V. For each curve, the lower HVCP power consumption is observed as the VCR increases.  $V_{\rm DBR}$  is the supply of the drivers in HVCP. As the required  $V_{\rm DBR}$  is reduced, the power consumption of the drivers reduces. In contrast, for the same VCR, the required  $V_{\rm DBR}$  is higher, resulting in higher power consumption of drivers and HVCP.

The pie charts in Fig. 12 show the average power consumption and silicon area of the main circuit blocks when the HVCP generates the highest output of 44 V with VCR = 12. As shown in Fig. 12a, the total average power consumption is 0.554 mW. More specifically, the HVCP has the highest power consumption (55%) followed by the voltage doubler (25%), other power management circuits (18%), and digital control circuit (2%). According to Fig. 12b, 87% of the total active silicon area is occupied by the HVCP. Table I summarizes the measured specifications of the IC.

#### V. DISCUSSION

Table II summarizes the performance of ultrasonic energy harvesting using pre-charged CMUT and compares it with state-of-the-art energy harvesting modalities used for IMDs. EM energy can propagate relatively long distances through the air. As shown in [20], the Tx antenna can deliver sufficient power at 10 cm away from the implant. However, the distance the EM propagates in tissue at high frequency (e.g., GHz bands) is much reduced. For example, the near-field inductive link approaches in [15-17] have limited power transmission distance, i.e., a few millimeters. For the applications that are not constrained to the

transcutaneous power transmission, EM WPT would be a simple setup as the EM WPT approach can typically tolerate an air gap between the Tx and the body. In contrast, the ultrasonic WPT requires acoustic contact at the Tx-body interface.

In EM wireless powering, as the Rx coil becomes smaller, the power carrier frequency needs to be increased to improve the Q-factor of the tiny coil. However, the tissue absorption rate increases along with the carrier frequency. In comparison to the EM WPT approach, ultrasound energy, which is typically at lower carrier frequencies, e.g., at a few MHz orders, has lowered attenuation in tissue. Hence, ultrasonic WPT can potentially substitute or complement the EM WPT approach when powering tiny implants in deep tissue (e.g., tens of millimeters).

The piezoelectric transducer is a common power Rx component in ultrasonic WPT setup [24-26]. The implant in [24] received sufficient ultrasonic power at the tissue depth of 10.5 cm. In [25] and [26], the ultrasonic-powered implants can operate safely in vivo at the tissue depth of 18 mm and 50 mm, respectively. The implants presented in [24-26] have a common feature that both the piezo and IC are bonded onto a substrate. Recently, CMUT has been shown to be a viable alternative to piezoelectric transducers because of its easy integration with circuits, CMUT-on-CMOS. The monolithic CMUT-on-CMOS approach also enables minimized parasitic. Driven by the need of shrinking the size of the implants, CMUTs can be used as the power Rx component in implants. However, CMUTs need a high bias voltage, such as several tens of volts to hundred volts. The recent emerging pre-charged CMUTs, which can relax the need for a high bias voltage significantly, enhance the wide use of CMUT power Rx in implants. Our proposed approach of precharged CMUT energy harvesting compares favorably with the existing piezo-based ultrasonic WPT approaches in terms of the moderate power transmission depth, the acoustic intensity, and the amount of power delivery to the IC.

We used a single-element commercial Tx transducer with a focal depth of 19 mm only for testing purposes. In the experimental characterization the goal is to have a spot size commensurate with the physical size of the receiving CMUT, a transmission frequency close to the center peak of the CMUT, and an acoustic intensity above the minimum acoustic intensity needed to operate the IC but below the FDA limit of 7.2 mW/mm². This is to characterize the performance of the power receiving unit. In a setting where the implant is deeper, we can

High voltage output

use a larger aperture Tx transducer focusing on the Rx to ensure the same acoustic intensity and spot size.

The ultrasonic power at the transducer surface is approximately 27.8 mW. As shown in Fig. 9, the amount of ultrasonic power received by the CMUT at 19 mm depth is 3.4 mW, and the usable electrical power delivered to the IC is 0.554 mW, yielding a PTE from ultrasonic power at the Tx transducer to electrical power at the IC of 2%. The total PTE is mainly influenced by the attenuation in media (such as tissue, oil, etc.), the electrical-to-acoustic power conversion efficiency of the Tx transducer, and the acoustic-to-electrical power conversion efficiency of the power Rx component (i.e., CMUT or piezo). The wireless powering PTE is limited by our current experimental setup due to the use of the commercial ultrasound Tx transducer. The ultrasonic powering PTE can be further improved by designing a custom Tx array and/or optimizing its conversion efficiency [27, 28].

In our current experimental setup, we need to first test the amount of trapped charge to decide the optimal DC bias needed for the pre-charged CMUT to maximize its output power. Then, we can set the target value of  $HV_{\rm OUT}$  to the optimal DC bias value by tuning the resistor in the voltage divider manually. In our future work, we will add on-chip auto-tuning of the resistor so that the IC will search for the optimal target voltage of  $HV_{\rm OUT}$  automatically. A viable operation process could be that in the default setting, the auto-tuning mechanism will set the target voltage of  $HV_{\rm OUT}$  to a value and increase the target voltage again once  $HV_{\rm OUT}$  reaches the voltage. Upon  $HV_{\rm OUT}$  reaches the collapse voltage of the pre-charged CMUT, the auto-tuning mechanism will reduce the target voltage of  $HV_{\rm OUT}$  by one step and stabilize it at its current status.

When WPT condition changes, e.g., misalignments, amount of transmitted power varying, and load varying, if the CMUT still can harvest sufficient power such that the HVCP can provide the optimal bias voltage, the closed-loop tuning control will dynamically adjust VCR to compensate for the wireless powering variations, stabilizing  $HV_{\rm OUT}$  at the optimal value. In cases that the CMUT cannot receive sufficient ultrasonic power, we need to adjust the amount of the transmitted power to compensate for the WPT variations. To do so, we will enable wireless data communication in our future work such that the IC will send the information of the received power to the Tx

| TABLE II: COMPARISON WITH STATE-OF-THE-ART ENERGY HARVESTING MODALITIES USED FOR IMDS |                                     |                                  |                                  |                      |                             |                              |                        |  |
|---|-------------------------------------|----------------------------------|----------------------------------|----------------------|-----------------------------|------------------------------|------------------------|--|
| Publications  | [15]                                | [16]                             | [17]                             | [20]                 | [24]                        | [25]                         | This Work              |  |
| Technology  | 350 nm CMOS                         | 65 nm CMOS                       | 130 nm CMOS                      | COTS                 | 180 nm HV<br>BCD            | 65 nm CMOS                   | 180 nm HV<br>BCD       |  |
| Wireless power modality   | 3-coil inductive link               | 2-coil inductive link            | 2-coil inductive link            | RF link              | Ultrasonic<br>link          | Ultrasonic<br>link           | Ultrasonic link        |  |
| Carrier frequency   | 60 MHz                              | 1 GHz                            | 1.3 GHz                          | 1.8 GHz,<br>2.9 GHz  | 1.314 MHz                   | 1.85 MHz                     | 2 – 6 MHz              |  |
| Power receiver  | Wire-wound coil,<br>1.6 mm diameter | On-chip coil,<br>500 µm diameter | On-chip coil,<br>200 µm diameter | Antenna              | Piezoelectric<br>transducer | Piezoelectric<br>transducer  | Pre-charged<br>CMUT    |  |
| Acoustic intensity  | N/A                                 | N/A                              | N/A                              | N/A                  | $2.9 \text{ mW/mm}^2$       | $> 56 \text{ mW/cm}^2$       | $3.78 \text{ mW/mm}^2$ |  |
| Medium  | Tissue                              | Tissue                           | Tissue                           | Air + Tissue         | Oil                         | Gel / Tissue                 | Oil                    |  |
| Transmission range  | 7 mm                                | 8 mm                             | 5 mm                             | 10 cm<br>through air | 10.5 cm                     | 70 mm (gel),<br>55 mm tissue | 19 mm                  |  |
| High DC voltage generator   | Voltage doubler                     | Rectifier                        | Charge pump rectifier            | Rectifier            | Charge pump                 | Rectifier                    | HVCP                   |  |

>1.2 V

TARLE II: COMPARISON WITH STATE-OF-THE-ART ENERGY HARVESTING MODALITIES LISED FOR IMDS

N/A

15 V

through the ultrasonic link while the Tx transducer adjusts the amount of transmitted power correspondingly.

The focus of this paper is on the design and measurement of the IC that interfaces with a pre-charged CMUT for ultrasonic energy harvesting. We characterized the IC specifications and demonstrated the proof-of-concept ultrasonic energy harvesting using the pre-charged CMUT. Implementation of a miniature (mm-sized) device with the CMUT and IC stacked together as shown in Fig. 1 is part of our future work. The HVCP design can also be readily extended to neural stimulation applications, where the stimulators need to have high compliance voltage to tolerate the voltage across the tissue-electrode interface impedance [39, 40]. With such feasibilities, the extension of the current IC to a wireless implantable stimulator is readily possible. Moreover, stimulators with modified form factors can be suited for certain stimulation targets, such as assembled with cuff electrodes for peripheral nerve stimulation [25].

### VI. CONCLUSION

We have presented an ultrasonic energy harvesting IC in which a novel low power, OVS robust, adaptive HVCP is implemented. To the best of our knowledge, this is the first IC that interfaces with pre-charged CMUT for ultrasonic energy harvesting. The circuit topology of the HVCP is chosen for not only power efficiency but also design simplicity and reliability. The proposed HVCP can generate an adjustable output voltage within the range of 4 V – 44 V, which can tolerate a wide variety of needs for bias voltage under different pre-charged CMUT conditions. Besides, the output voltage can be stabilized to a target voltage by the closed-loop VCR tuning mechanism in the presence of wireless power conditions varying.

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Ömer Oralkan is an inventor on patents related to CMUT fabrication on glass substrates and a co-founder of ClearSens, Inc., Morrisville, NC, USA, which has licensed some of these patents.

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